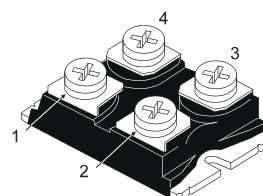


NPN DARLINGTON POWER MODULE

- HIGH CURRENT POWER BIPOLAR MODULE
- VERY LOW R_{th} JUNCTION TO CASE
- SPECIFIED ACCIDENTAL OVERLOAD AREAS
- ULTRAFAST FREEWHEELING DIODE
- ISOLATED CASE (2500V RMS)
- EASY TO MOUNT
- LOW INTERNAL PARASITIC INDUCTANCE

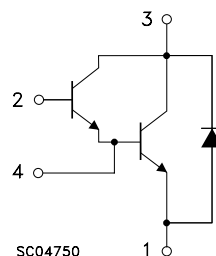
INDUSTRIAL APPLICATIONS:

- MOTOR CONTROL
- UPS
- DC/DC & DC/AC CONVERTERS



ISOTOP

INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CEV}	Collector-Emitter Voltage ($V_{BE} = -5\text{ V}$)	150	V
$V_{CEO(sus)}$	Collector-Emitter Voltage ($I_B = 0$)	120	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	7	V
I_C	Collector Current	120	A
I_{CM}	Collector Peak Current ($t_p = 10\text{ ms}$)	180	A
I_B	Base Current	2	A
I_{BM}	Base Peak Current ($t_p = 10\text{ ms}$)	4	A
P_{tot}	Total Dissipation at $T_c = 25\text{ }^{\circ}\text{C}$	175	W
T_{stg}	Storage Temperature	-55 to 150	$^{\circ}\text{C}$
T_j	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$
V_{iso}	Insulation Withstand Voltage (AC-RMS)	2500	$^{\circ}\text{C}$

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case (transistor)	Max	0.7	°C/W
R _{thj-case}	Thermal Resistance Junction-case (diode)	Max	0.9	°C/W
R _{thc-h}	Thermal Resistance Case-heatsink With Conductive Grease Applied	Max	0.05	°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CER} #	Collector Cut-off Current (R _{BE} = 5 Ω)	V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _j = 100 °C			1.5 10	mA mA
I _{CEV} #	Collector Cut-off Current (V _{BE} = -5V)	V _{CE} = V _{CEV} V _{CE} = V _{CEV} T _j = 100 °C			1 7	mA mA
I _{EBO} #	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V			1	mA
V _{CEO(SUS)} *	Collector-Emitter Sustaining Voltage	I _C = 5 A L = 15 mH V _{clamp} = 125 V	125			V
h _{FE} *	DC Current Gain	I _C = 100 A V _{CE} = 5 V		1200		
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 70 A I _B = 0.25 A I _C = 70 A I _B = 0.25 A T _j = 100 °C I _C = 100 A I _B = 1 A I _C = 100 A I _B = 1 A T _j = 100 °C		1.25 1.35 1.5 1.65	1.5 2	V V V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 100 A I _B = 1 A I _C = 100 A I _B = 1 A T _j = 100 °C		2.3 2.35	3	V V
di _C /dt	Rate of Rise of On-state Collector	V _{CC} = 90 V R _C = 0 t _p = 3 μs I _{B1} = 0.5 A T _j = 100 °C	200	230		A/μs
V _{CE} (3 μs) •	Collector-Emitter Dynamic Voltage	V _{CC} = 90 V R _C = 1.3 Ω I _{B1} = 0.5 A T _j = 100 °C		2	3	V
V _{CE} (5 μs) •	Collector-Emitter Dynamic Voltage	V _{CC} = 90 V R _C = 1.3 Ω I _{B1} = 0.5 A T _j = 100 °C		1.8	2.5	V
t _s t _f t _c	Storage Time Fall Time Cross-over Time	I _C = 70 A V _{CC} = 90 V V _{BB} = -5 V R _{BB} = Ω V _{clamp} = 125 V I _{B1} = 0.25 A L = 60 μH T _j = 100 °C		0.9 0.15 0.3	2 0.3 0.6	μs μs μs
V _{CEW}	Maximum Collector Emitter Voltage Without Snubber	I _{CWoff} = 120 A I _{B1} = 1A V _{BB} = -5 V V _{CC} = 90 V L = 60 μH R _{BB} = 1.25 Ω T _j = 125 °C	125			V
V _F *	Diode Forward Voltage	I _F = 100 A T _j = 100 °C		0.92	1	V
I _{RM}	Reverse Recovery Current	V _{CC} = 125 V I _F = 100 A di _F /dt = -200 A/μs L < 0.05 μH T _j = 100 °C		10	14	A

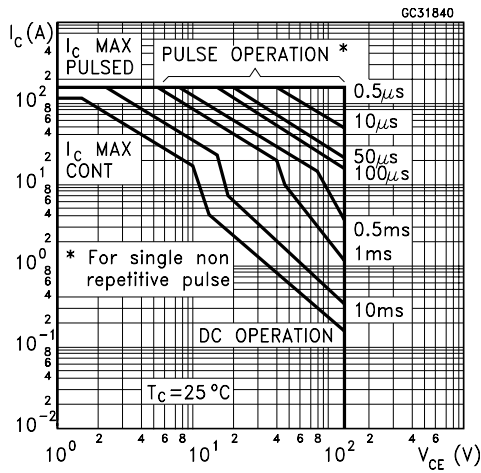
* Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

See test circuits in databook introduction

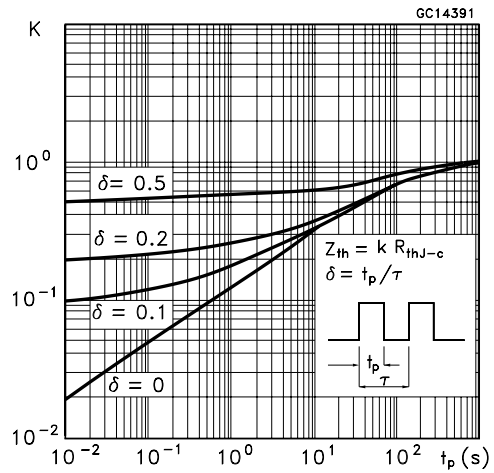
To evaluate the conduction losses of the diode use the following equations:

$$V_F = 0.66 + 0.0034 I_F \quad P = 0.66 I_{F(AV)} + 0.0034 I_{F(RMS)}^2$$

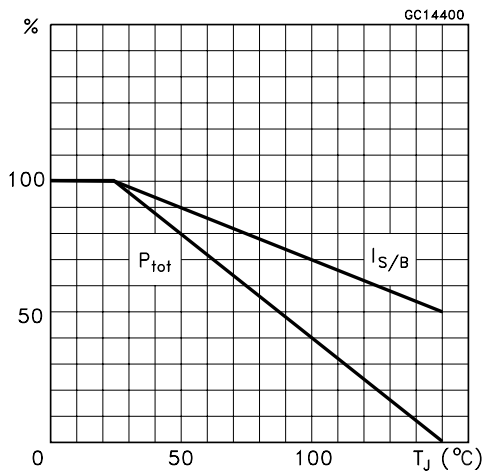
Safe Operating Areas



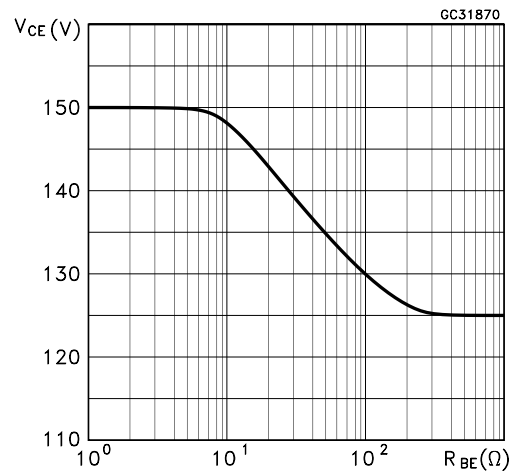
Thermal Impedance



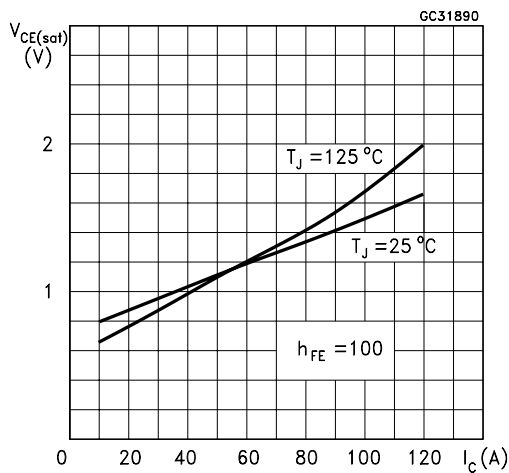
Derating Curve



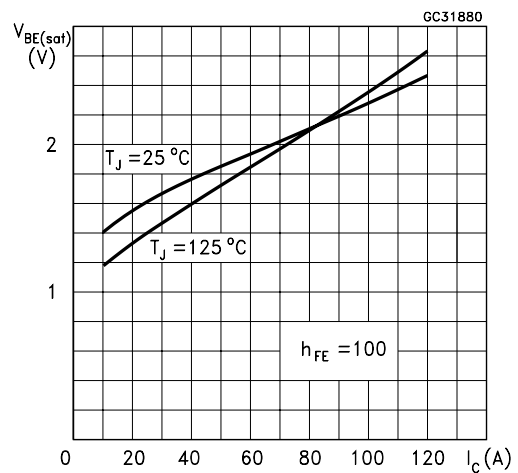
Collector-emitter Voltage Versus base-emitter Resistance



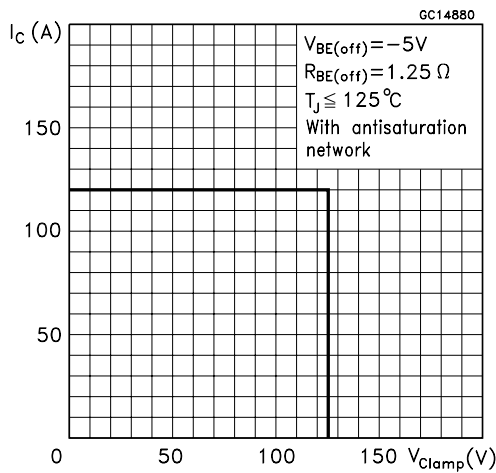
Collector Emitter Saturation Voltage



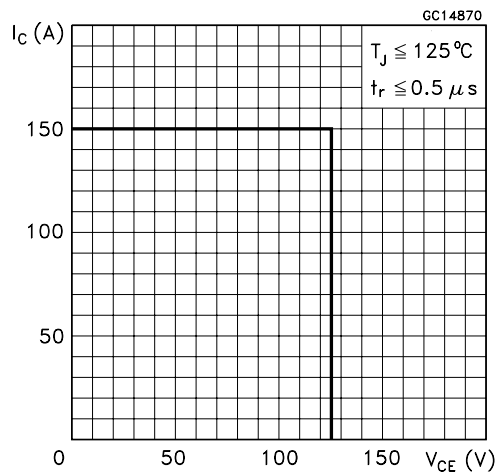
Base-Emitter Saturation Voltage



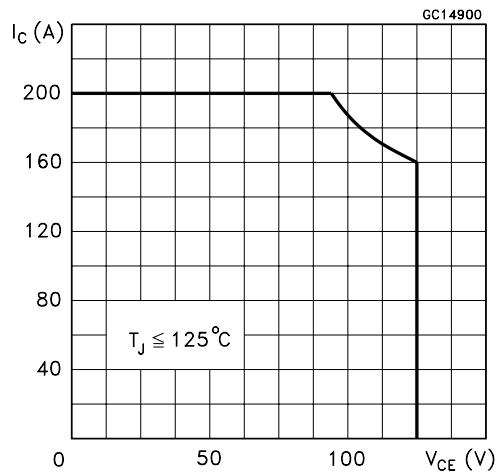
Reverse Biased SOA



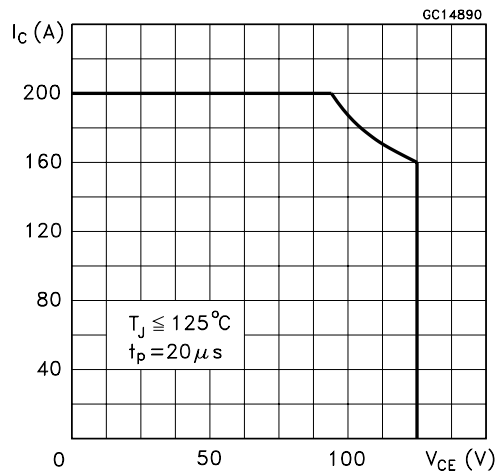
Forward Biased SOA



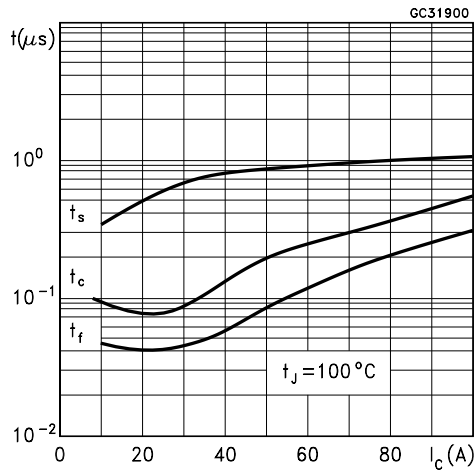
Reverse Biased AOA



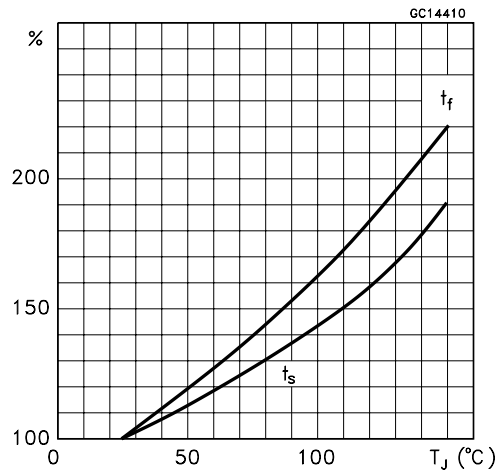
Forward Biased AOA



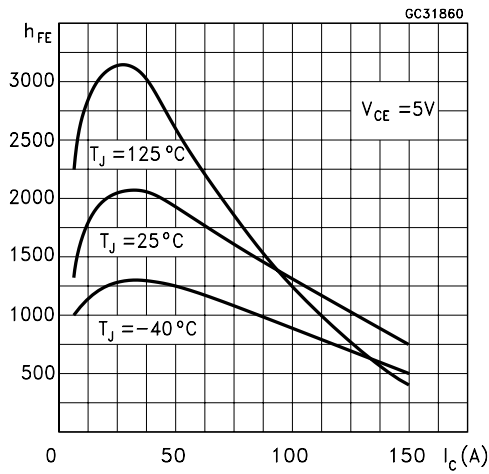
Switching Times Inductive Load



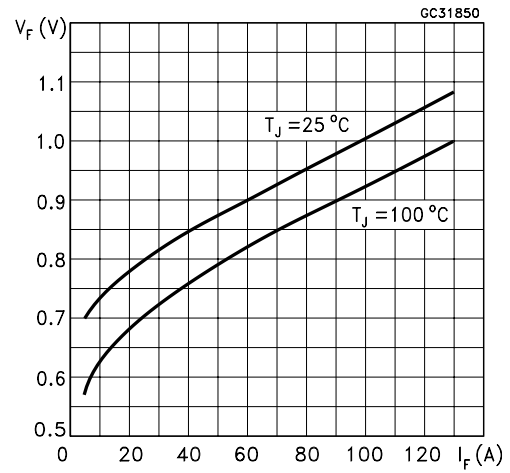
Switching Times Inductive Load Versus Temperature



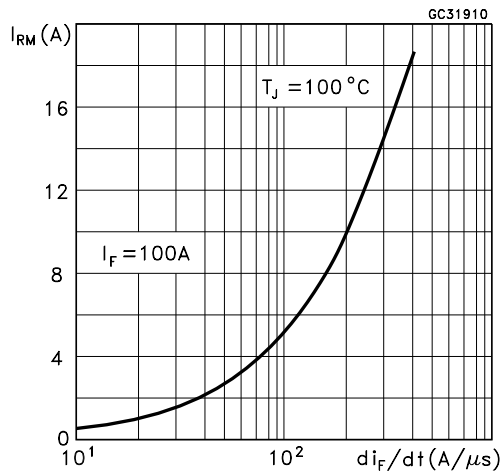
Dc Current Gain



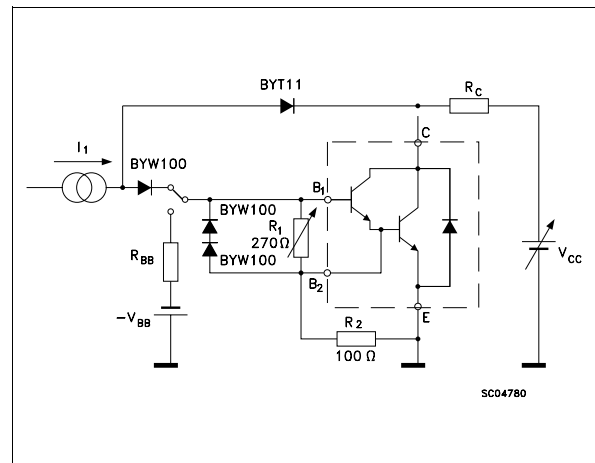
Typical V_F Versus I_F



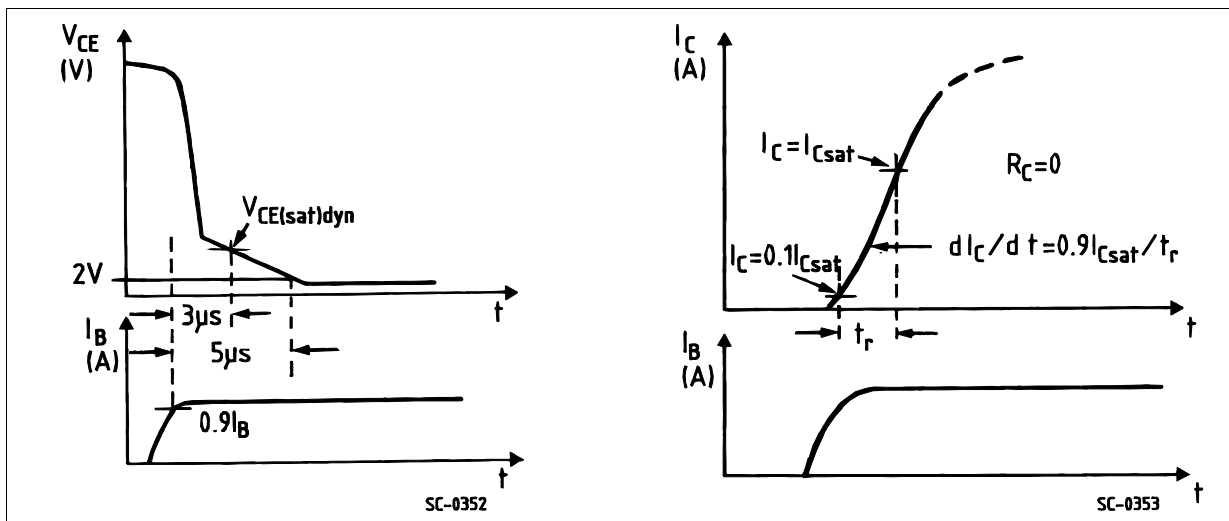
Peak Reverse Current Versus di_F/dt



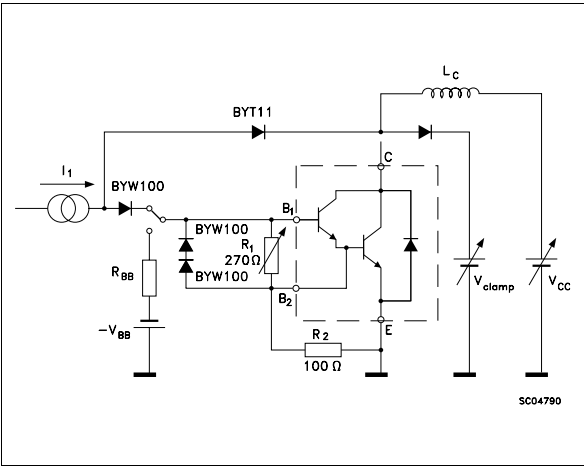
Turn-on Switching Test Circuit



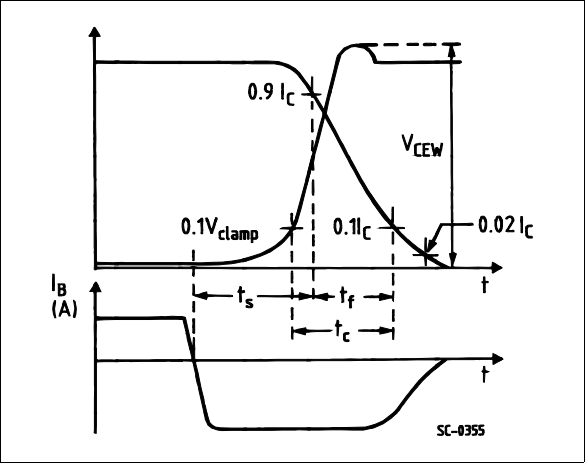
Turn-on Switching Waveforms



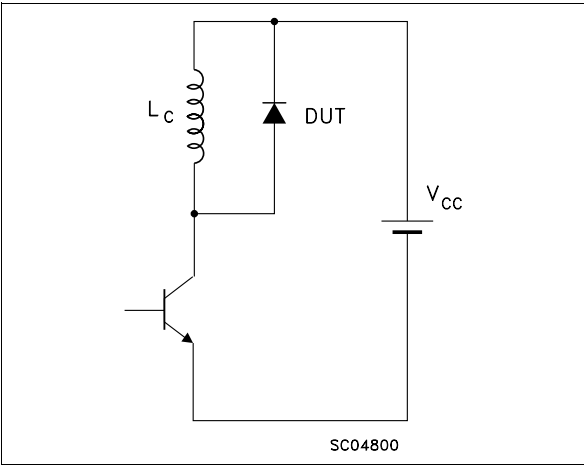
Turn-on Switching Test Circuit



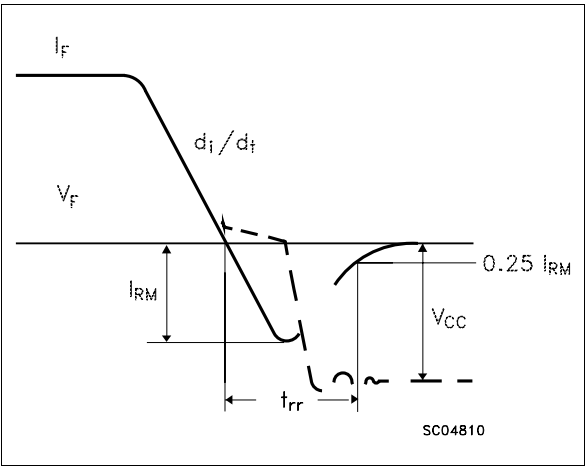
Turn-off Switching Waveforms



Turn-off Switching Test Circuit of Diode

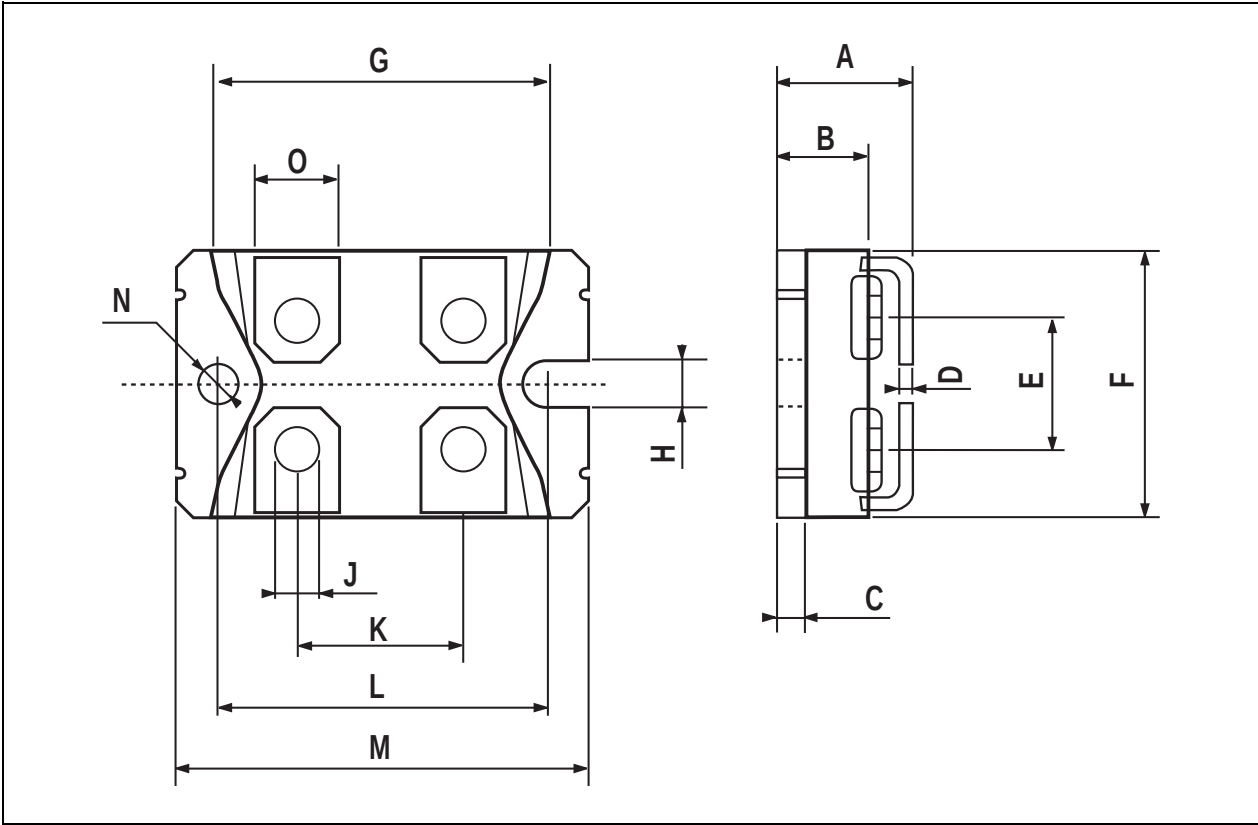


Turn-off Switching Waveform of Diode



ISOTOP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	11.8		12.2	0.466		0.480
B	8.9		9.1	0.350		0.358
C	1.95		2.05	0.076		0.080
D	0.75		0.85	0.029		0.033
E	12.6		12.8	0.496		0.503
F	25.15		25.5	0.990		1.003
G	31.5		31.7	1.240		1.248
H	4			0.157		
J	4.1		4.3	0.161		0.169
K	14.9		15.1	0.586		0.594
L	30.1		30.3	1.185		1.193
M	37.8		38.2	1.488		1.503
N	4			0.157		
O	7.8		8.2	0.307		0.322



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